

Innovative silicon timing sensors for the future ALICE 3 experiment

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LGADs (Low Gain Avalanche Detectors)

LGAD ased on internal Low-gain (Drift region p epi-laye Low and unifo p⁺⁺ substrate

GAD

Time Res

60

50

40

30

20

10

70

Evolution of *n*-on-*p* sensors, obtained by implanting a Gain region Very high doped **gain layer** just below the *p*-*n* junction electric field



double-LGAD introduced and tested for the first time https://doi.org/10.1140/epjp/s 13360-023-04621-x

 \rightarrow signals of both layers sum up resulting in a *larger* signal (charge) using a *single* front-end amplifier

the double-LGAD w.r.t. single LGAD \leftarrow





SiPMs (Silicon Photomultipliers)

SiPM as array of O(10⁴) **SPAD**s (Single Photon Avalanche Detectors) in Geiger mode (gain 10⁶) above breakdown

ALICE

Direct response of SiPMs to the passage of charged particles was studied for the first time





First prototype (MadPix) with integrated electronics and gain layer produced by LFoundry in 110 nm commercial process

Active thickness: 48 µm

p-p-well

High Resistivity Si

- Backside HV allows full depletion -25 V to -40 V
- Topside HV controls the gain 30 V to 60 V





